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Diodes Incorporated DMN3016LPS-13

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DMN3016LPS

30V N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI<sup>®</sup>

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON) max</sub>	$I_D$ $T_A = +25^{\circ}C$		
30V	$12m\Omega @ V_{GS} = 10V$	10.8A		
300	$16m\Omega @ V_{GS} = 4.5V$	9.5A		

# **Description and Applications**

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

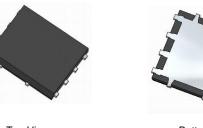
- DC-DC Converters
- Power Management Functions
- Analog Switch

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile Ideal for Thin Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

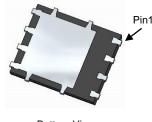
# **Mechanical Data**

- Case: POWERDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.097 grams (Approximate)

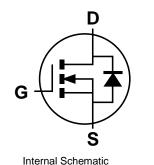
POWERDI5060-8

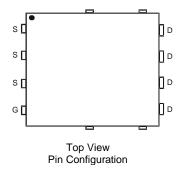


Top View









### Ordering Information (Note 4)

Case	Packaging
POWERDI5060-8	2500 / Tape & Reel
	POWERDI5060-8

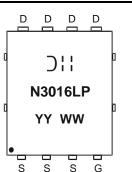
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



)' | = Manufacturer's Marking
N3016LP = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Digit of Year (ex: 14 = 2014)
WW = Week Code (01 to 53)

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# DMN3016LPS

#### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V <sub>DSS</sub>	30	V		
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	10.8 8.5	A
	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	15.5 12.3	А
	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	9.5 7.5	A
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$	t<10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	13.5 10.8	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	70	А
Avalanche Current (Note 7) L = 0.1mH			I <sub>AS</sub>	22	A
Avalanche Energy (Note 7) L = 0.1mH			E <sub>AS</sub>	24	mJ

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)		PD	1.18	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Devi	109	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	R <sub>0JA</sub>	49	°C/W
Total Power Dissipation (Note 6)		PD	2.75	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	46	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	R <sub>0JA</sub>	24	°C/W
Thermal Resistance, Junction to Case (Note 6)	R <sub>0JC</sub>	4.5	°C/W	
Operating and Storage Temperature Range	T <sub>J.</sub> T <sub>STG</sub>	-55 to +150	°C	

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)						-	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	1	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.4	-	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	P	-	8.5	12	12 mΩ	$V_{GS} = 10V, I_D = 20A$	
	R <sub>DS (ON)</sub>	-	10.5	16	11152	$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	V <sub>SD</sub>	-	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	-	1415	-	pF		
Output Capacitance	Coss	-	119	-	pF	− V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, − f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	82	-	pF	1 - 1.00012	
Gate Resistance	R <sub>g</sub>	-	3.0	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	-	11.3	-	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	-	25.1	-	nC		
Gate-Source Charge	Q <sub>gs</sub>	-	3.5	-	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 12A	
Gate-Drain Charge	Q <sub>gd</sub>	-	3.6	-	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	-	4.8	-	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V, R <sub>L</sub> = 1.25Ω, R <sub>G</sub> = 3Ω	
Turn-On Rise Time	t <sub>R</sub>	-	16.5	-	ns		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	26.1	-	ns		
Turn-Off Fall Time	tF	-	5.6	-	ns	7	
Reverse Recovery Time	t <sub>RR</sub>	-	12.3	-	ns		
Reverse Recovery Charge	Q <sub>rr</sub>	-	10.4	-	nC	I <sub>F</sub> = 12A, di/dt = 500A/μs	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. Notes:

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

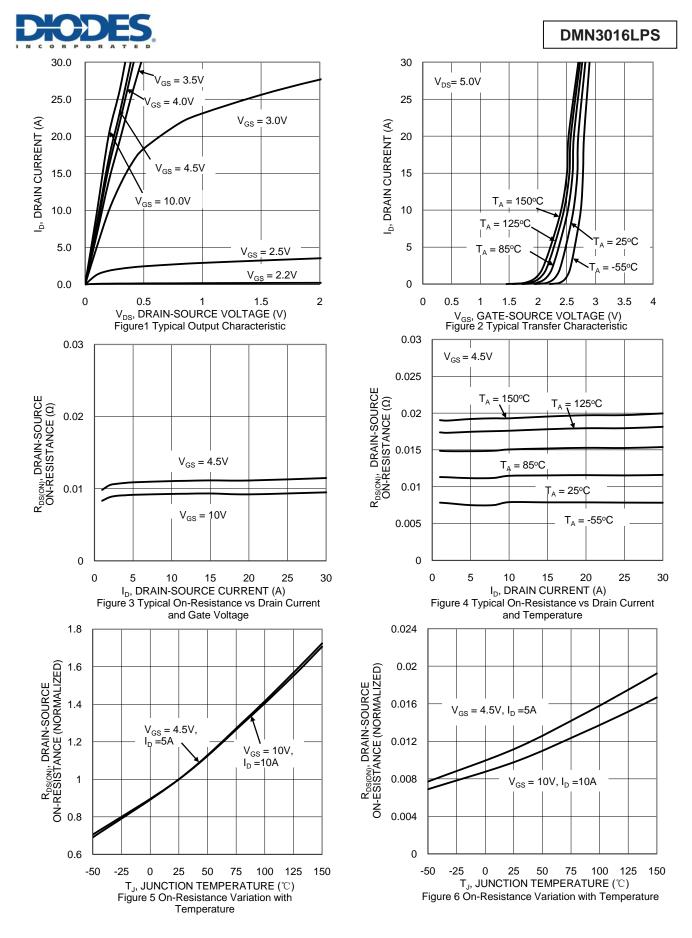
7. I<sub>AS</sub> and E<sub>AS</sub> rating are based on low frequency and duty cycles to keep  $T_J$  = +25°C.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

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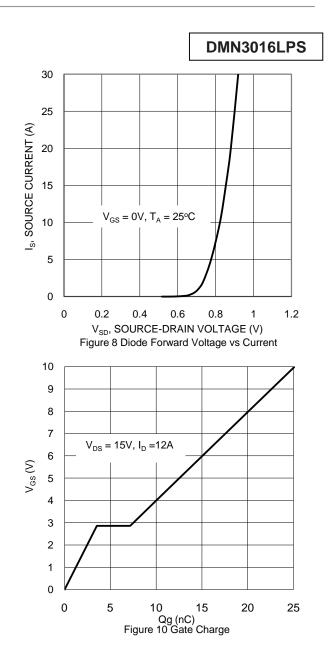




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3 V<sub>GS(TH)</sub>, GATE THESHOLD VOLTAGE (V) 2.5 2  $I_D = 1 m A$ 1.5 1  $I_D = 250 \mu A$ 0.5 0 -25 0 50 75 100 125 -50 25 150 T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Figure 7 Gate Theshold Variation vs Junction Temperature 10000 f=1MHz C<sub>T</sub>, JUNCTION CAPACITANCE (pF) 1000 Ciss Coss 100 C<sub>rss</sub> 10 0 2 4 6 8 10 12 14 16 18 20 V<sub>ps</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 9 Typical Junction Capacitance 100 R<sub>DS(ON)</sub> Limited I<sub>D</sub>, DRAIN CURRENT (A) 1 1 D F P<sub>w</sub> =100ms T<sub>J(Max)</sub>=150℃ T<sub>A</sub>=25℃ P<sub>w</sub>: =10ms V<sub>GS</sub>=10V =1ms Single Pulse DUT on 1\*MRP Board =100µs 0.01 0.1 10 100 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 11 SOA, Safe Operation Area

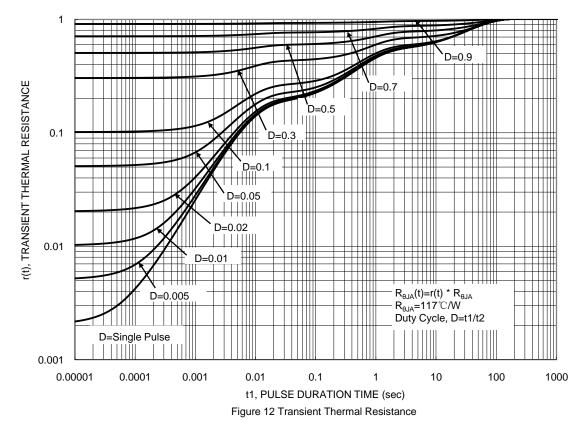


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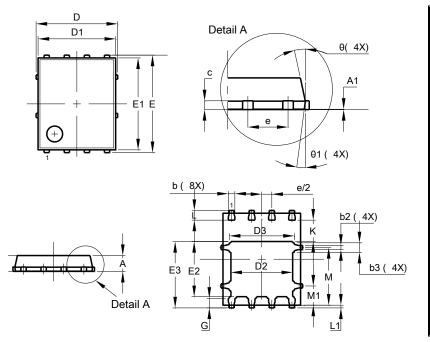


DMN3016LPS

# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### (1) Package Type: POWERDI<sup>®</sup>5060-8

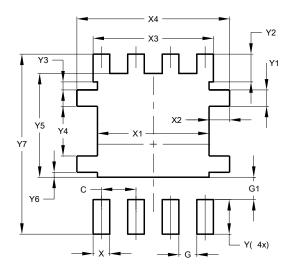


POWERDI <sup>®</sup> 5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05			
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
c	0.230	0.330	0.277		
D	5.15 BSC				
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Ш	(	6.15 BSC			
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
e		1.27 BSC			
G	0.51	0.71	0.61		
K	0.51				
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
Μ	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10º	12º	11º		
Θ1	6º	8º	7°		
Al	All Dimensions in mm				

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

(1) Package Type: POWERDI<sup>®</sup>5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
X3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			





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